

## 1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



**Product data sheet** 

# 1. Product profile

### 1.1 General description

Ultrafast epitaxial rectifier diode in a SOD113 (TO-220F) plastic package.

#### 1.2 Features

- Fast switching
- Soft recovery characteristic
- Low forward voltage drop
- Low thermal resistance
- Isolated package

### 1.3 Applications

- High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM)Power Factor Correction (PFC)

### 1.4 Quick reference data

- V<sub>RRM</sub> ≤ 600 V
- V<sub>F</sub> ≤ 1.11 V

- $I_{F(AV)} \le 5 A$
- $t_{rr} \le 60 \text{ ns}$

# 2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode (k)		
2	anode (a)	mb	k — <b>├</b> a <i>001aaa020</i>
mb	mounting base; isolated		
		SOD113 (2-lead TO-220	OF)



# 3. Ordering information

### Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BYV25X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113

# 4. Limiting values

### Table 3. Limiting values

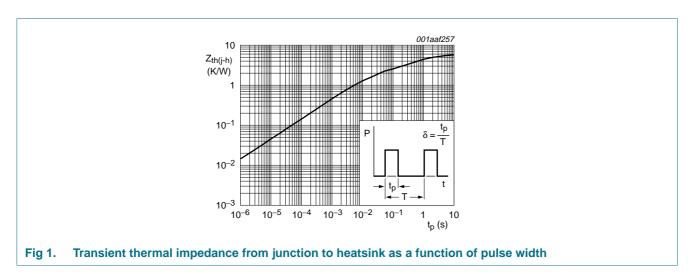
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	square waveform; $\delta$ = 1.0; $T_h \le 100$ °C	-	600	V
I <sub>F(AV)</sub>	average forward current	square waveform; $\delta$ = 0.5; $T_h \le$ 115 °C	-	5	Α
I <sub>FRM</sub>	repetitive peak forward current	square waveform; $\delta$ = 0.5; $T_h \le$ 115 °C	-	10	Α
I <sub>FSM</sub>	non-repetitive peak forward	t = 10 ms; sinusoidal waveform	-	60	Α
	current	t = 8.3 ms; sinusoidal waveform	-	66	Α
T <sub>stg</sub>	storage temperature		-40	+150	°C
T <sub>i</sub>	junction temperature		-	150	°C

# 5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 1	-	-	5.5	K/W
		without heatsink compound	-	-	5.9	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



### 6. Isolation characteristics

### Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$  unless otherwise specified.

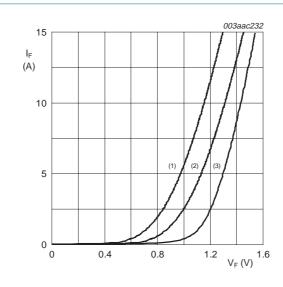
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all terminals to external heatsink; $f = 50 \text{ Hz}$ to 60 Hz; sinusoidal waveform; relative humidity $\leq 65 \%$ ; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

# 7. Characteristics

Table 6. Characteristics

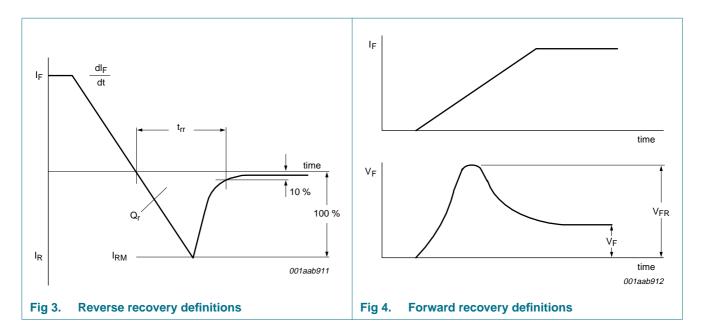
 $T_i = 25 \,^{\circ}C$  unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>F</sub>	forward voltage	$I_F = 5 \text{ A}$ ; $T_j = 150 ^{\circ}\text{C}$ ; see Figure 2	-	0.97	1.11	V
		I <sub>F</sub> = 5 A	-	1.12	1.30	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V	-	2	50	μΑ
		$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.1	0.35	mA
Dynamic o	haracteristics					
Q <sub>r</sub>	recovered charge	$I_F$ = 2 A to $V_R$ $\geq$ 30 V; $dI_F/dt$ = 20 A/ $\mu$ s; see Figure 3	-	40	70	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A to V}_R \ge 30 \text{ V};$ $dI_F/dt = 100 \text{ A/}\mu\text{s}; \text{ see } \underline{\text{Figure 3}}$	-	50	60	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F$ = 10 A to $V_R$ $\geq$ 30 V; $dI_F/dt$ = 50 A/ $\mu$ s; $T_j$ = 100 °C; see Figure 3	-	3	5.5	Α
$V_{FR}$	forward recovery voltage	$I_F = 10 \text{ A}$ ; $dI_F/dt = 10 \text{ A/}\mu\text{s}$ ; see Figure 4	-	3.2	-	V



- (1)  $T_j = 150 \,^{\circ}\text{C}$ ; typical values
- (2)  $T_i = 150 \,^{\circ}\text{C}$ ; maximum values
- (3)  $T_j = 25$  °C; maximum values

Fig 2. Forward current as a function of forward voltage



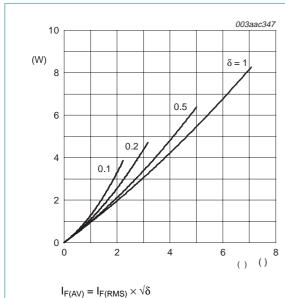


Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values

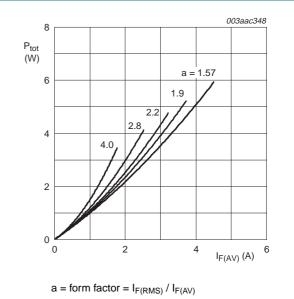
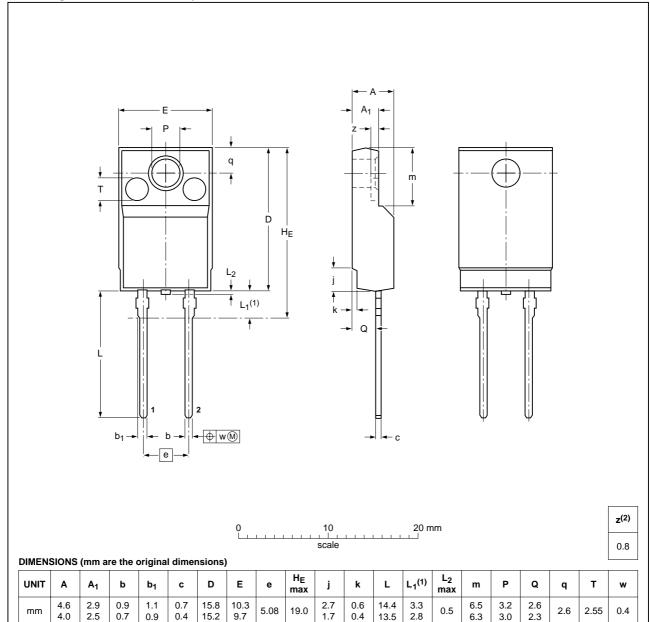


Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

# 8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

SOD113



#### Notes

- 1. Terminals are uncontrolled within zone L<sub>1</sub>.
- 2. z is depth of T.

OUTLINE VERSION		REFER	ENCES	EUROPEAN	ISSUE DATE
	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOD113		2-lead TO-220F			<del>02-04-09</del> 07-06-18

Fig 7. Package outline SOD113 (2-lead TO-220F)

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# 9. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV25X-600_1	20080812	Product data sheet	-	-

# 10. Legal information

#### 10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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